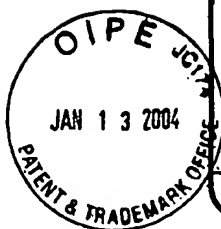


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Sheet 1 of 2

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Application Number	10/693,846
Filing Date	10/20/03
First Named Inventor	August et al.
Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	84.785

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

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Date Considered

11/27/04

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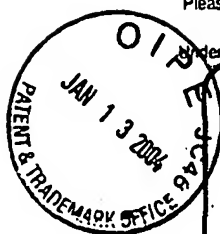
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Sheet 2

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Application Number	10/693,846
Filing Date	10/20/03
First Named Inventor	August et al.
Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	84,785

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Dkg		MCGREGOR et al, "Self-Biased Boron-10 Coated High-Purity Epitaxial GaAs Thermal Neutron Detector" IEEE transactions on nuclear science, vol. 47, no., August 2000	
Dkg		MCGREGOR et al, "Recent Results From Thin-Film-Coated Semiconductor Neutron Detectors" X-Ray and Gamma-Ray Detector and Application IV, vol. 4784 (2002)	
Dkg		HAQUE et al, "Neutron dosimetry employing soft errors in dynamic random access memories" Phys. Med. Biol., 1989 vol. 34, no 9, 1195-1202 Printed in the UK	
Dkg		PHILLIPS et al, "Feasibility of a Neutron Detector-Dosimeter Based on Single-Event Upsets in Dynamic Random-Access Memories" Radiation Protection Dosimetry vol. 101, nos. 1-4, pp. 129-132 (2002) Nuclear Technology Publishing	
Dkg		ROBERTSON et al, "A class of boron-rich solid-state neutron detectors" Applied Physics Letters volume 80, number 19, 13 May 2002	
Dkg		GUARINI et al, "Electrical Integrity of State-of-the-Art 0.13-um SOI CMOS Devices and Circuits Transferred for Three-Dimensional (3D) Integrated Circuit (IC) Fabrication" 0-7803-7462-2/02 2002 IEEE	
Dkg		ARITA et al, "Experimental Investigation of Thermal Neutron-Induced Single Event Upset in Static Random Access Memories" Jpn. J. Appl. Phys Vol. 40 (2001) pp. L151-L153 Part 2, No. 2B, 15 February 2001	
Dkg		HUGHES et al, "Radiation Effects and Hardening of Mos Technology: Devices and Circuits" Preprint IEEE Trans. Nucl. Sci. June 2003	
Dkg		LUND et al, "Neutron Dosimeter Using a Dynamic Random Access Memory as a Sensor" IEEE Transactions on Nuclear Science, Vol. 33, No. 1, February 1996	
Dkg		PETERSEN et al, "Calculation of Cosmic-Ray Induced Soft Upsets and Scaling in VLSI Devices*" IEEE Transaction on Nuclear Science, Vol. NS-29, No. 6, December 1982	
Dkg		DAVIS "Use of Computer-Memory Chips as The Basis For a Digital Albedo Neutron Dosimeter*" Health Physics Vol. 49, No. 2 (August), pp. 259-265, 1985 Printed in the U.S.A.	

Examiner Signature	<i>Doug E. Owa</i>	Date Considered	11/27/04
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